





TN6707A

NPN General Purpose Amplifier

• These devices is designed for general purpose medium power amplifiers and switches requiring collector currents to 1.0A WWW.BZSU • Sourced from process 39.

TO-226

TN6707A

Absolute Maximum Ratings* TA=25°C unless otherwise noted

Symbol	Parameter	FPN660	Units
V _{CEO}	Collector-Emitter Voltage	80	V
V _{CBO}	Collector-Base Voltage	100	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	1.2	A
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 ~ +150	°C

These ratings of any semiconductor device may be impaired

NOTES:

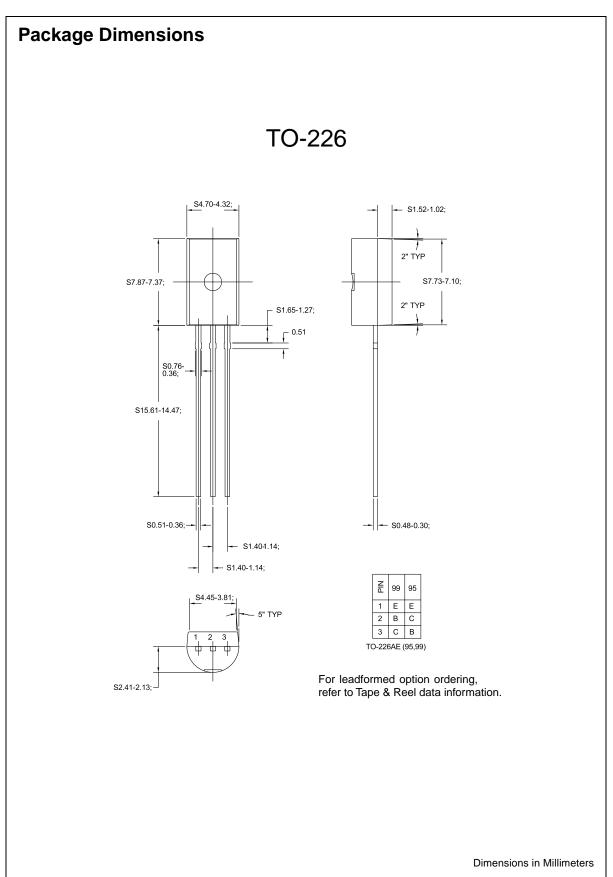
These ratings are based on a maximum junction temperature of 150°C.
These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics TA=25°C unless otherwise noted

	Test Conditions	Min.	Max.	Units
teristics	164 1900	and N	1.0	
Collector-Emitter Breakdown Voltage *	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$	80		V
Collector-Base Breakdown Voltage	$I_{\rm E} = 100\mu A, I_{\rm E} = 0$	100		V
Emitter-Base Breakdown Voltage	$I_{\rm E} = 1.0 {\rm mA}, I_{\rm C} = 0$	5.0		V
Collector-Base Cutoff Current	$V_{CB} = 80V, I_{F} = 0$		0.1	μΑ
Emitter-Base Cutoff Current	$V_{EB} = 5.0V, I_{C} = 0$		0.1	μΑ
teristics *		•		
DC Current Gain	$V_{CE} = 2.0V, I_{C} = 50mA$	40		
	$V_{CE} = 2.0V, I_{C} = 250mA$	40	250	-
	$V_{CE} = 2.0V, I_{C} = 500mA$	25		30
Collector-Emitter Saturation Voltage	I _C = 500mA, I _B = 50mA	7	0.5	V
-	I _C = 1.0A, I _B = 100mA	137	1.0	V
Base-Emitter On Voltage	V _{CE} = 2.0V, I _C = 1.0A	Level V	1.5	V
al Characteristics	00.913.125	100		
Output Capacitance	V _{CE} = 5.0V, I _C = 200mA, f = 20MHz	2.5	20	MHz
Current Gain Bandwidth Product	$V_{CE} = 5.0V, I_{C} = 50mA, f = 20MHz$	50		MHz
	Collector-Emitter Breakdown Voltage * Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage Collector-Base Cutoff Current Emitter-Base Cutoff Current teristics * DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter On Voltage al Characteristics Output Capacitance	Collector-Emitter Breakdown Voltage * $I_C = 10mA$, $I_B = 0$ Collector-Base Breakdown Voltage $I_E = 100\muA$, $I_E = 0$ Emitter-Base Breakdown Voltage $I_E = 1.0mA$, $I_C = 0$ Collector-Base Cutoff Current $V_{CB} = 80V$, $I_E = 0$ Emitter-Base Cutoff Current $V_{CB} = 5.0V$, $I_C = 0$ teristics *DC Current GainDC Current Gain $V_{CE} = 2.0V$, $I_C = 50mA$ $V_{CE} = 2.0V$, $I_C = 500mA$ Collector-Emitter Saturation Voltage $I_C = 500mA$, $I_B = 50mA$ $I_C = 1.0A$, $I_B = 100mA$ Base-Emitter On Voltage $V_{CE} = 2.0V$, $I_C = 1.0A$ Output Capacitance $V_{CE} = 5.0V$, $I_C = 200mA$, $f = 20MHz$	Collector-Emitter Breakdown Voltage * $I_C = 10mA$, $I_B = 0$ 80Collector-Base Breakdown Voltage $I_E = 10\muA$, $I_E = 0$ 100Emitter-Base Breakdown Voltage $I_E = 1.0mA$, $I_C = 0$ 5.0Collector-Base Cutoff Current $V_{CB} = 80V$, $I_E = 0$ 5.0Emitter-Base Cutoff Current $V_{CB} = 5.0V$, $I_C = 0$ 5.0teristics * $V_{CE} = 2.0V$, $I_C = 50mA$ 40DC Current Gain $V_{CE} = 2.0V$, $I_C = 50mA$ 40 $V_{CE} = 2.0V$, $I_C = 500mA$ 25Collector-Emitter Saturation Voltage $I_C = 500mA$, $I_B = 50mA$ 25Base-Emitter On Voltage $V_{CE} = 2.0V$, $I_C = 1.0A$ 40al Characteristics $V_{CE} = 5.0V$, $I_C = 200mA$, $f = 20MHz$ 2.5	Collector-Emitter Breakdown Voltage * $I_C = 10mA$, $I_B = 0$ 80Collector-Base Breakdown Voltage $I_E = 100\muA$, $I_E = 0$ 100Emitter-Base Breakdown Voltage $I_E = 1.0mA$, $I_C = 0$ 5.0Collector-Base Cutoff Current $V_{CB} = 80V$, $I_E = 0$ 0.1Emitter-Base Cutoff Current $V_{CB} = 5.0V$, $I_C = 0$ 0.1Emitter-Base Cutoff Current $V_{EB} = 5.0V$, $I_C = 0$ 0.1Emitter-Base Cutoff Current $V_{CE} = 2.0V$, $I_C = 50mA$ 40DC Current Gain $V_{CE} = 2.0V$, $I_C = 50mA$ 40 $V_{CE} = 2.0V$, $I_C = 500mA$ 2525Collector-Emitter Saturation Voltage $I_C = 500mA$, $I_B = 50mA$ 0.5 $I_C = 1.0A$, $I_B = 100mA$ 1.01.5Base-Emitter On Voltage $V_{CE} = 2.0V$, $I_C = 1.0A$ 1.5Cultput Capacitance $V_{CE} = 5.0V$, $I_C = 200mA$, $f = 20MHz$ 2.5

Thermal Characteristics TA=25°C unless otherwise noted

Symbol	Parameter	Max.	Units
PD	Total Device Dissipation	1.0	W
	Derate above 25°C	8.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	50	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	125	°C/W



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